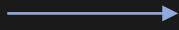
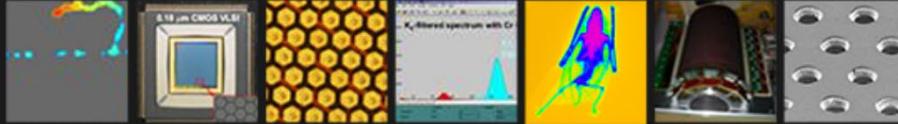


RD51 Collaboration



DRD1 Collaboration

Prospects for VMM4

for Applications in the DRD1 Collaboration

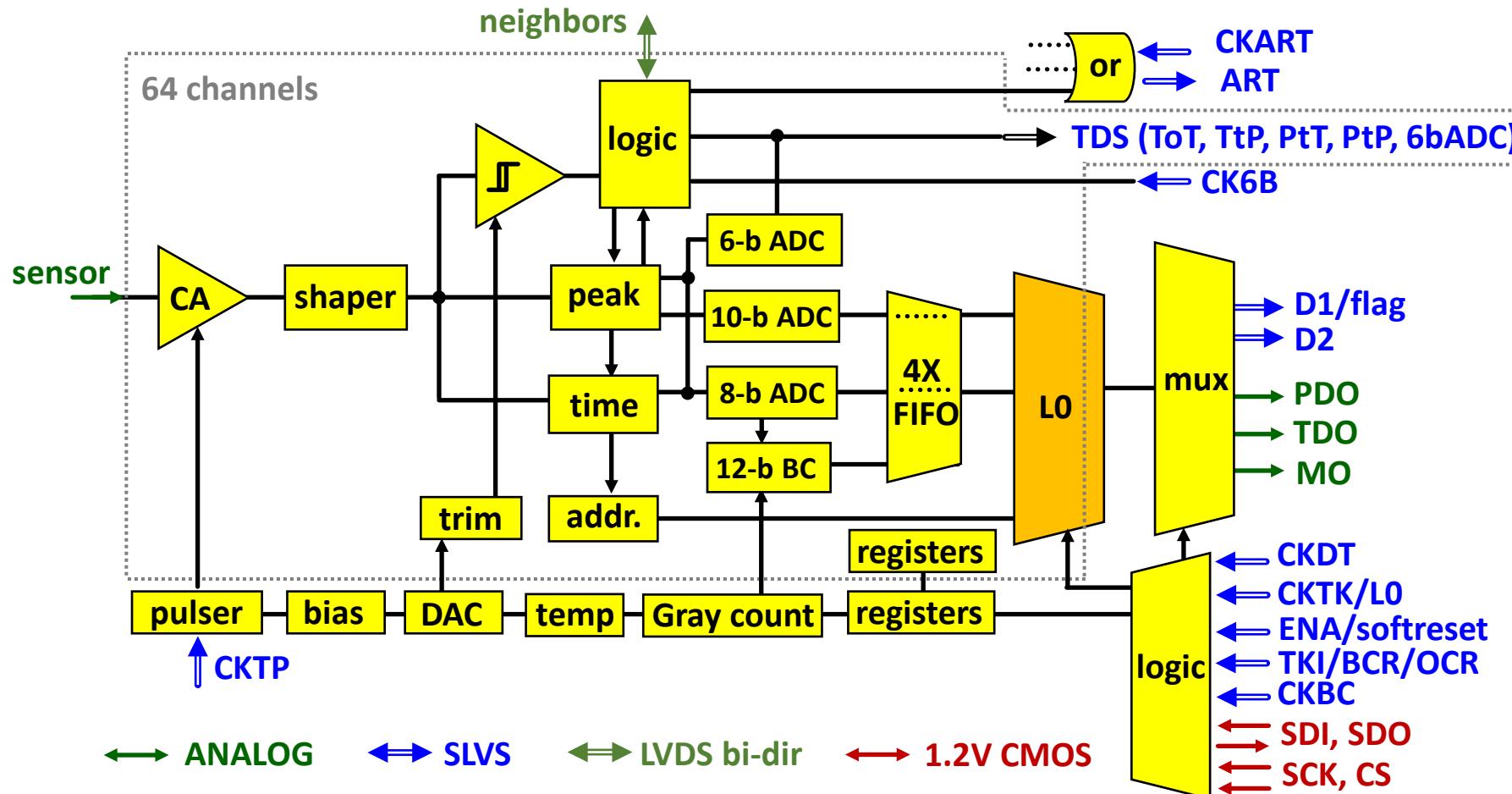
Gianluigi De Geronimo

Stony Brook University, University of Michigan, DG Circuits
degeronimo@ieee.org

Outline

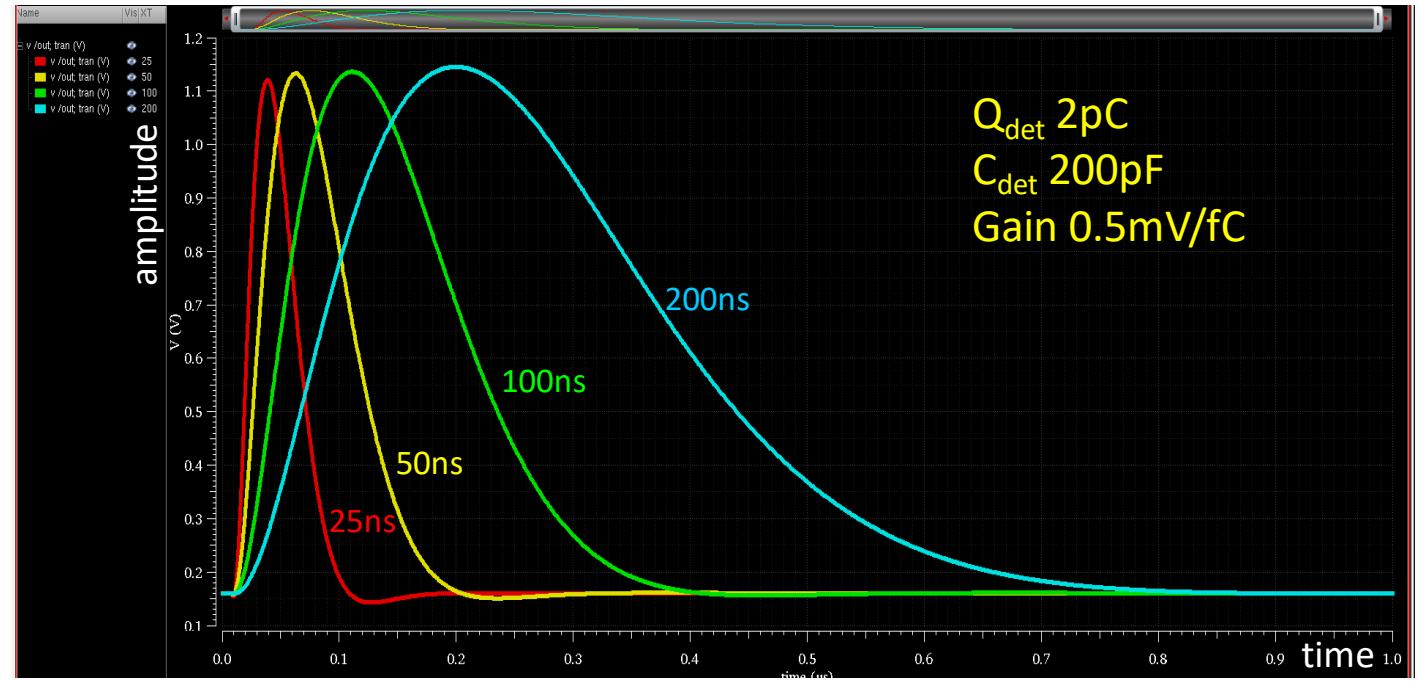
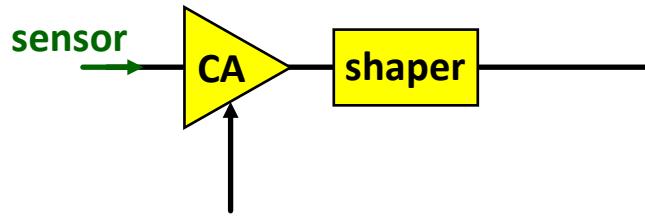
- **VMM3a:** architecture, performance, limitations
- Prospects for **VMM4**

VMM3a Architecture



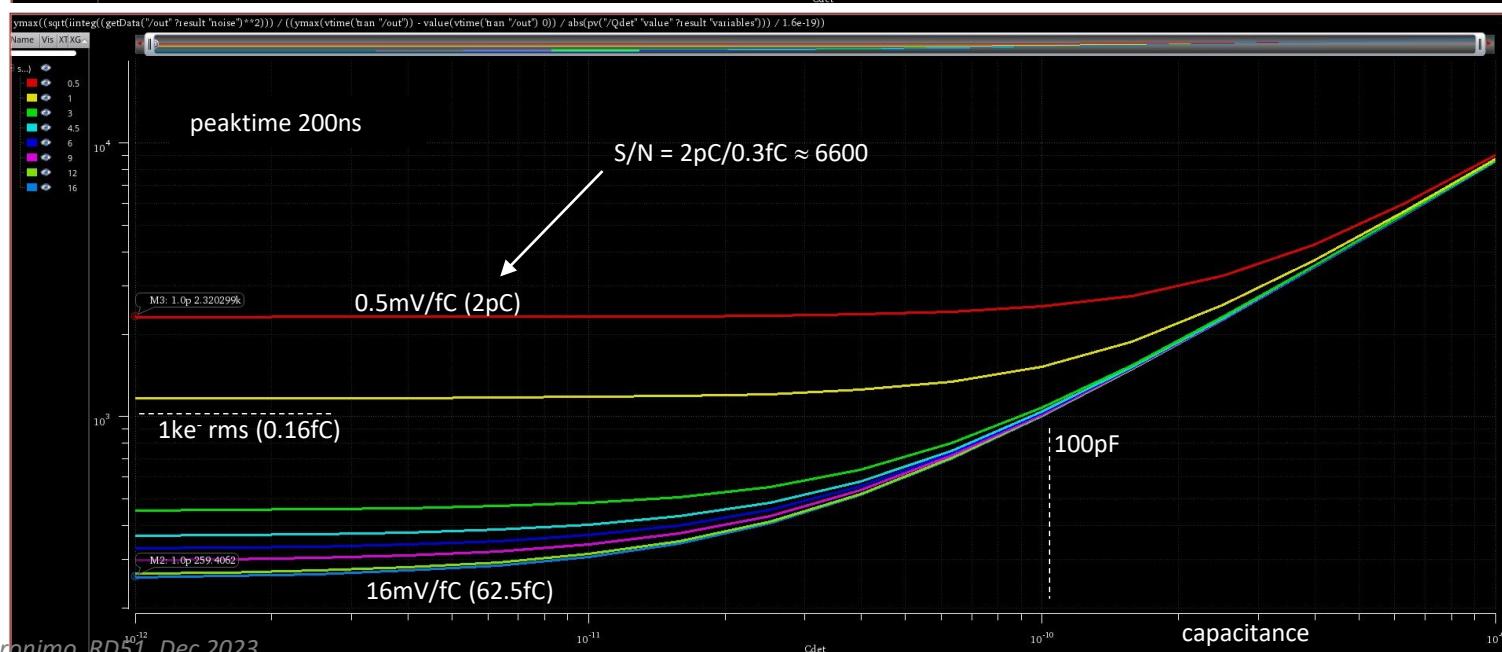
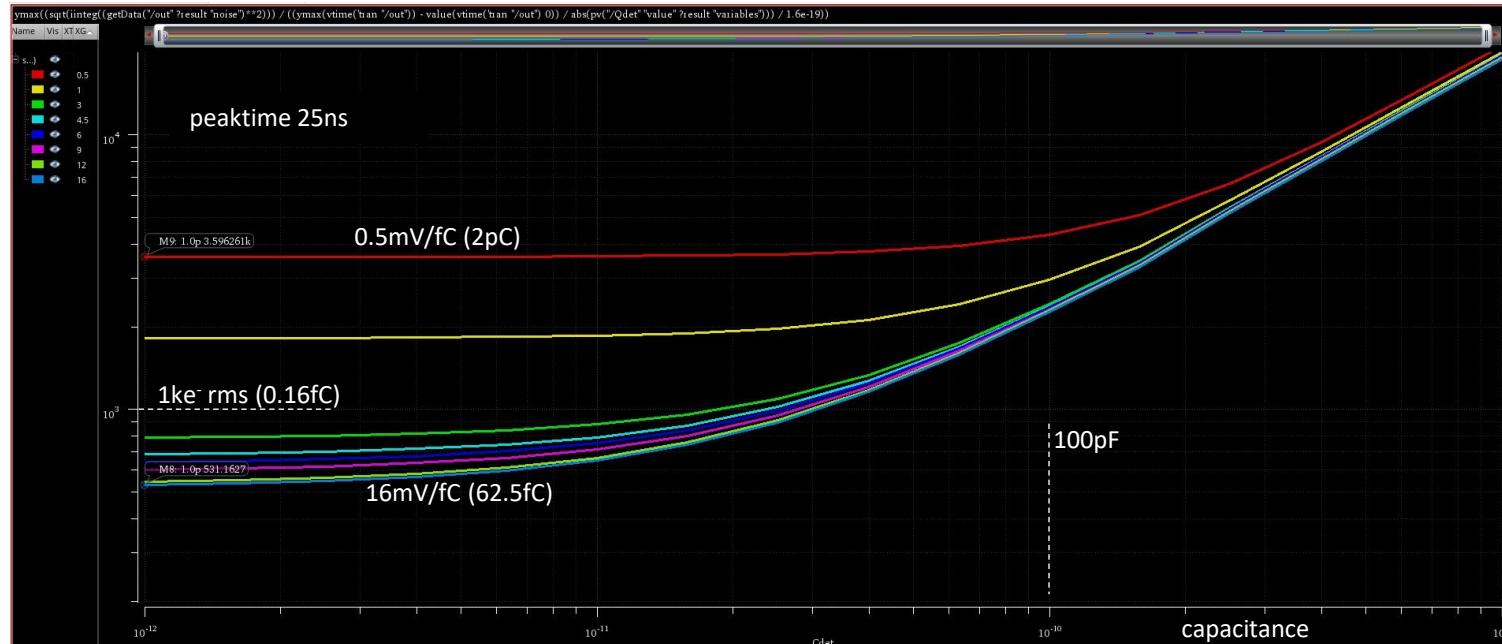
- high-functionality and high-programmability front-end ASIC
- designed for multiple NSW detectors, also adopted outside ATLAS
- efficient charge and timing measurements with high throughput

Analog Front-End

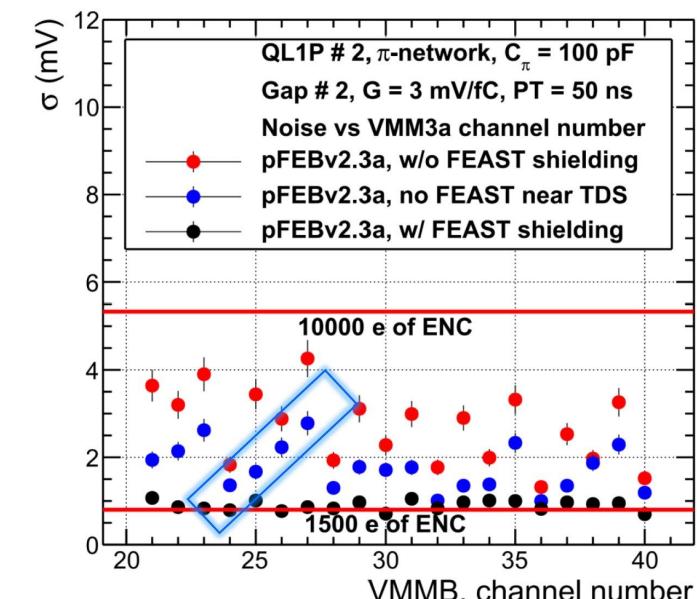
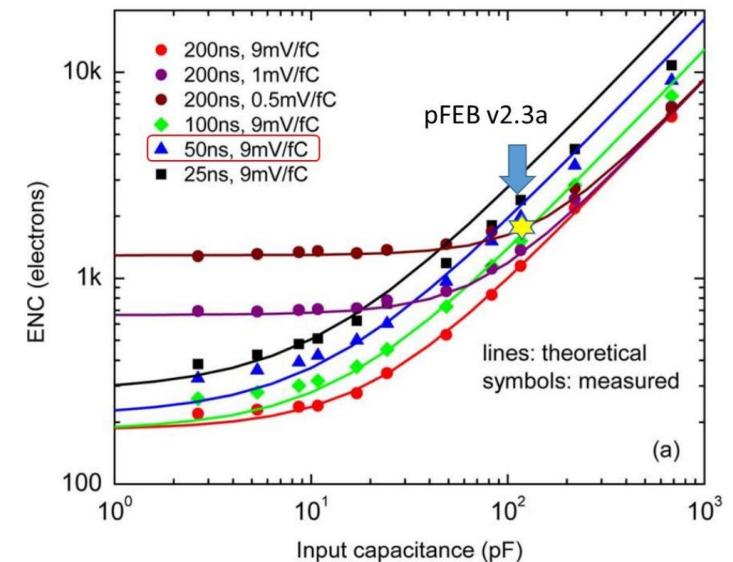


- input transistor: PMOS 180nm x 20mm, 2mA
- input capacitance: optimized for 200pF, can operate from **sub-pF to several nF**
- adjustable charge polarity: **positive, negative**
- adjustable gain: **0.5, 1, 3, 4.5, 6, 9, 12, 16 mV/fC**
- maximum charge: linear up to **2pC**, fast recovery from **50pC**
- adjustable peaking time: **25, 50, 100, 200 ns**
- ion tail compensation: off, mild, strong
- leakage-adaptive, high-leakage modes, DDF low-noise shaper, BGR-stabilized baseline, test capacitor, mask, ...

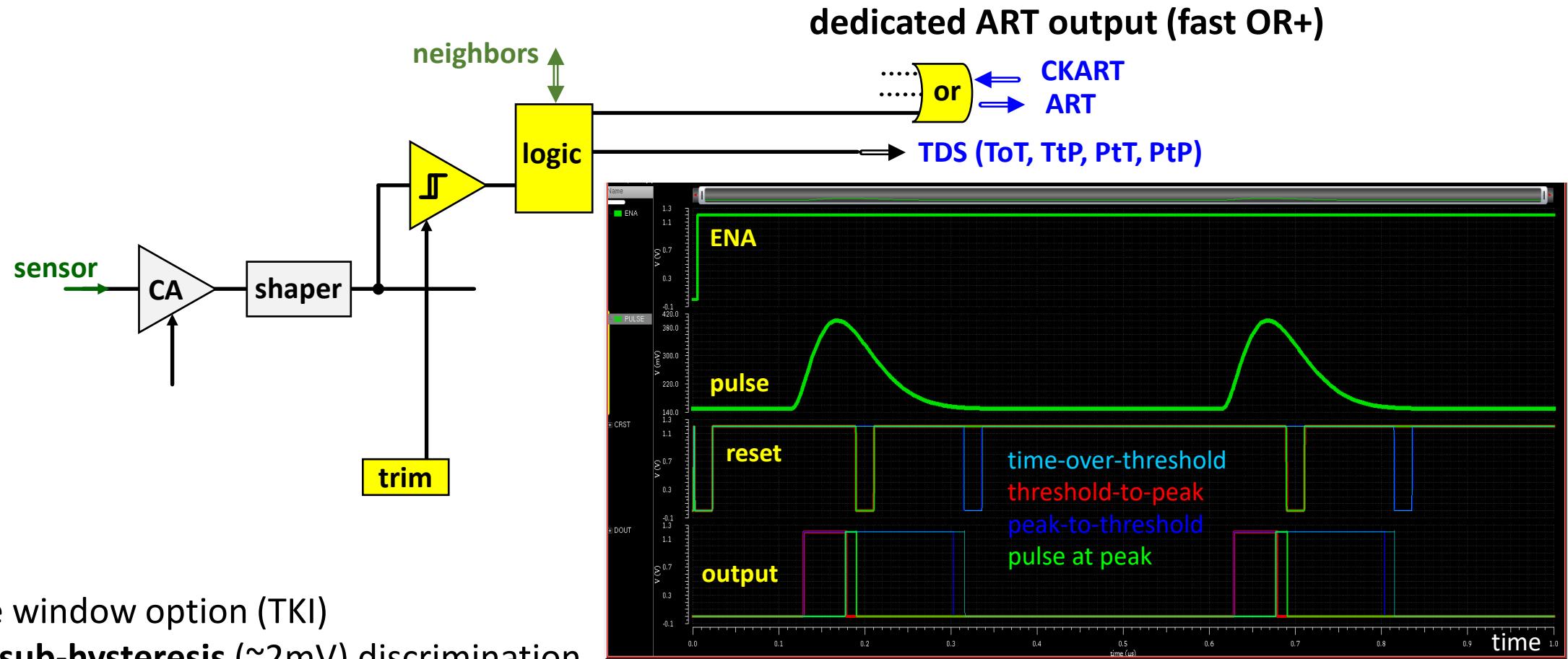
Equivalent Noise Charge



simulations (user reference)
example measurements (environment-dependent)

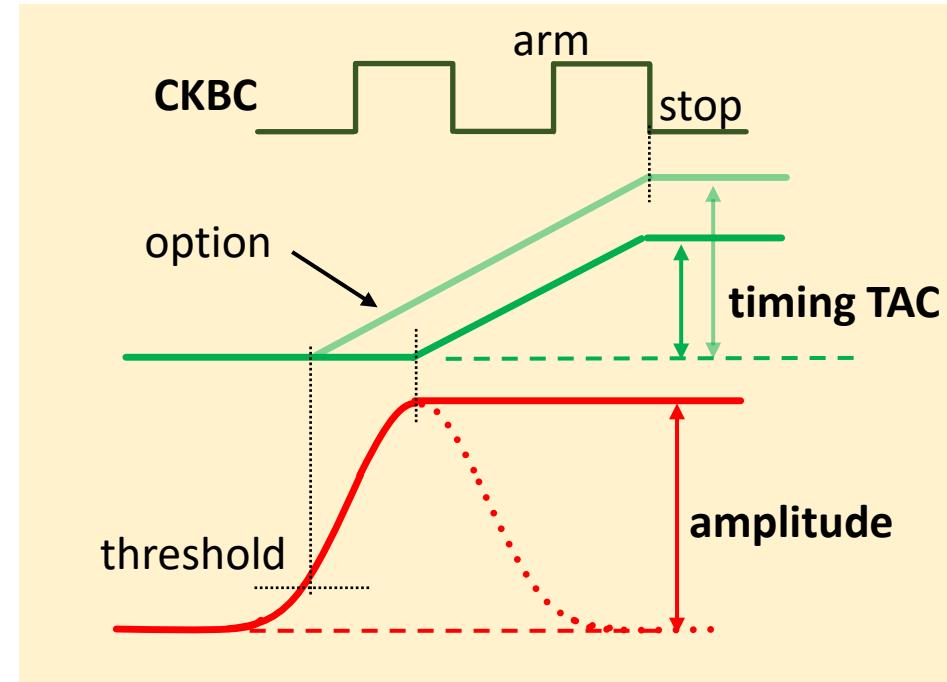
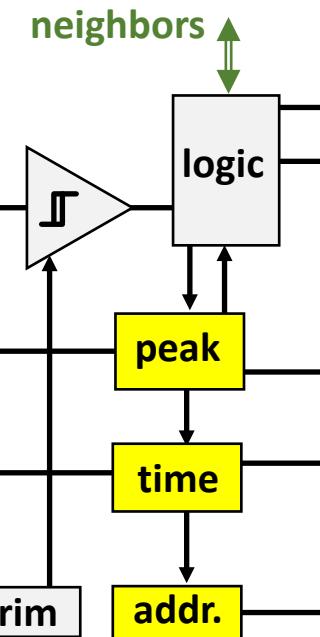
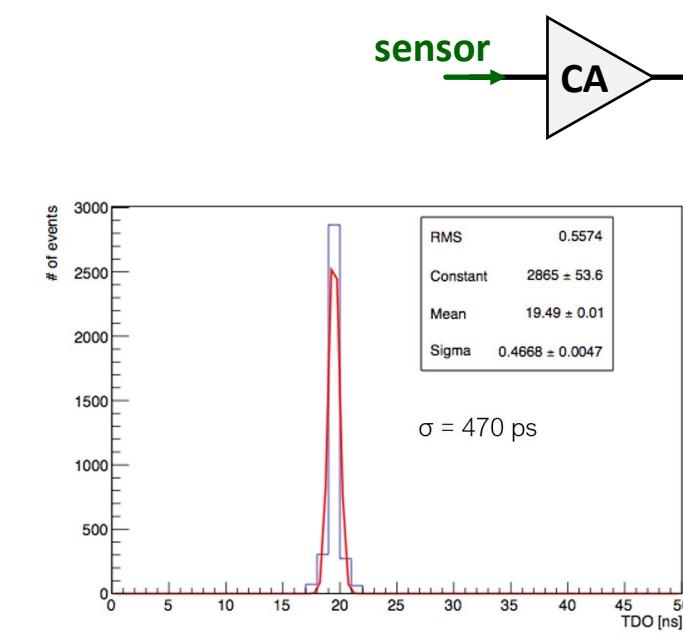
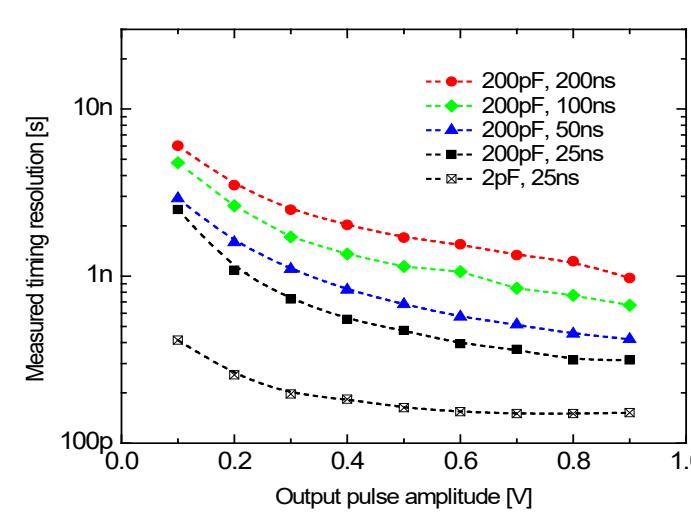


Discrimination, Direct Outputs, Address in Real Time (ART)



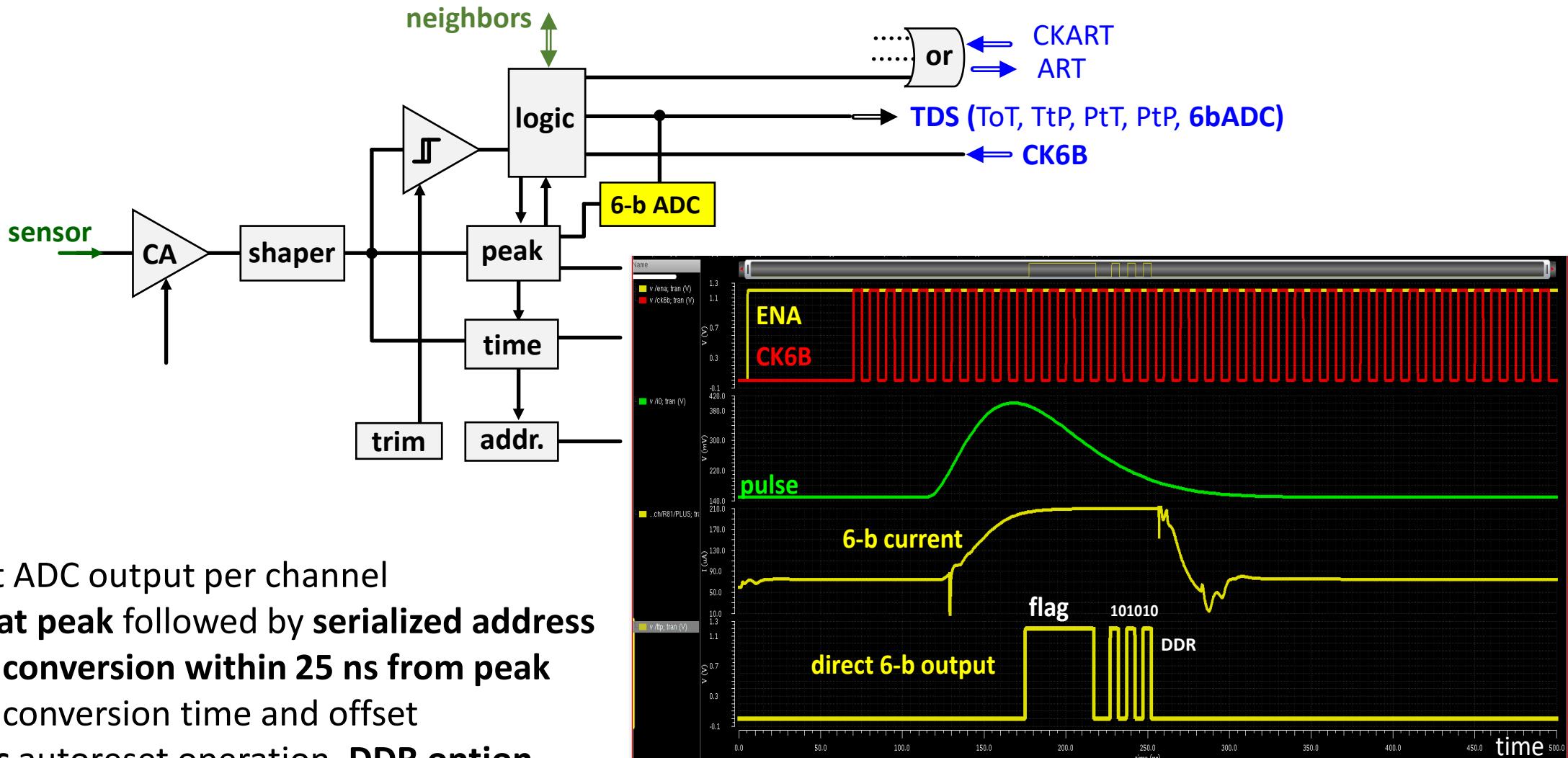
- acceptance window option (TKI)
- trimmable **sub-hysteresis** ($\sim 2\text{mV}$) discrimination
- neighbor channels acquisition: **sub-threshold neighbors** with **inter-chip communication**
- flag with serialized **first address in real time** (ART) with dedicated output, **DDR option**, sync option
- **direct SLVS output per channel** with programmable measurements:
 - **time-over-threshold ToT, threshold-to-peak TtP, peak-to-threshold PtT, pulse-at-peak PtP**

Peak and Time Detection

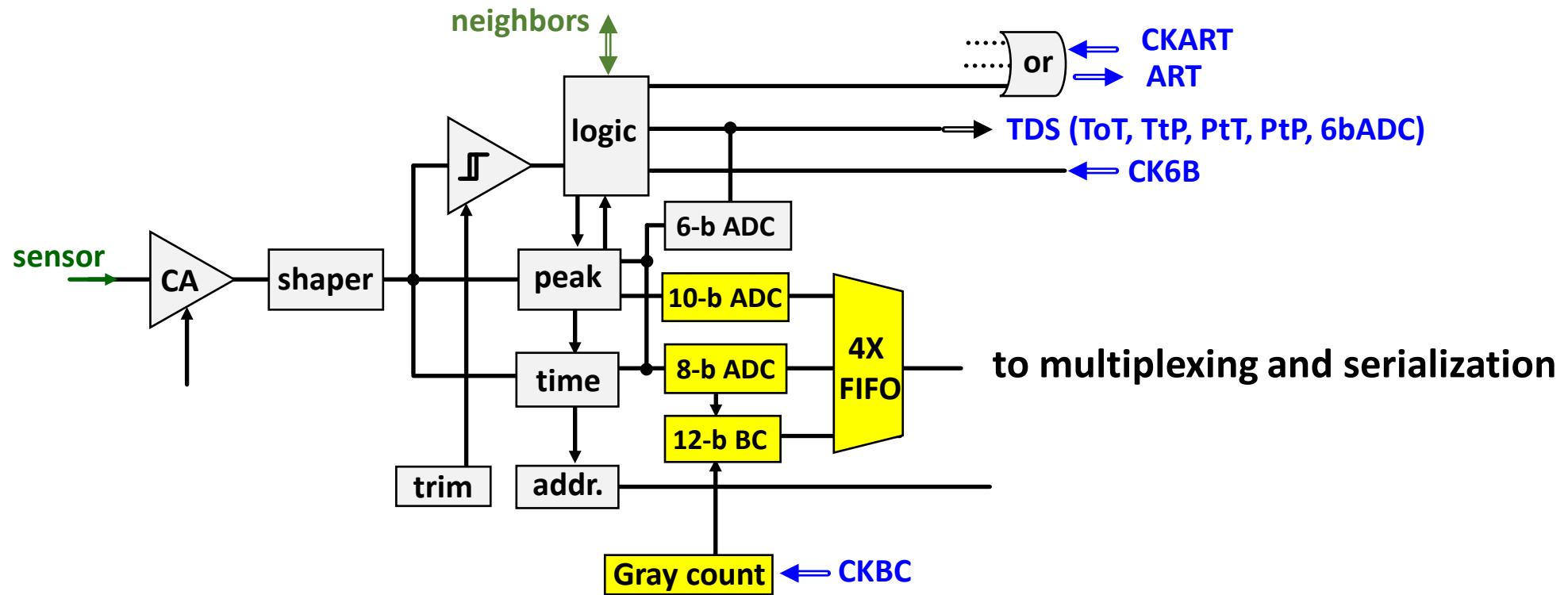


- peak detection: measurement of peak amplitude (charge) and storage in analog memory
- time detection: measurement of **peak timing (sub-200ps, low time-walk)**, TAC and storage in analog memory
- optional **timing at threshold**, adjustable time-to-amplitude conversion (**TAC**): 60, 100, 350, 650 ns

Lower-Resolution Direct 6-bit ADC Outputs

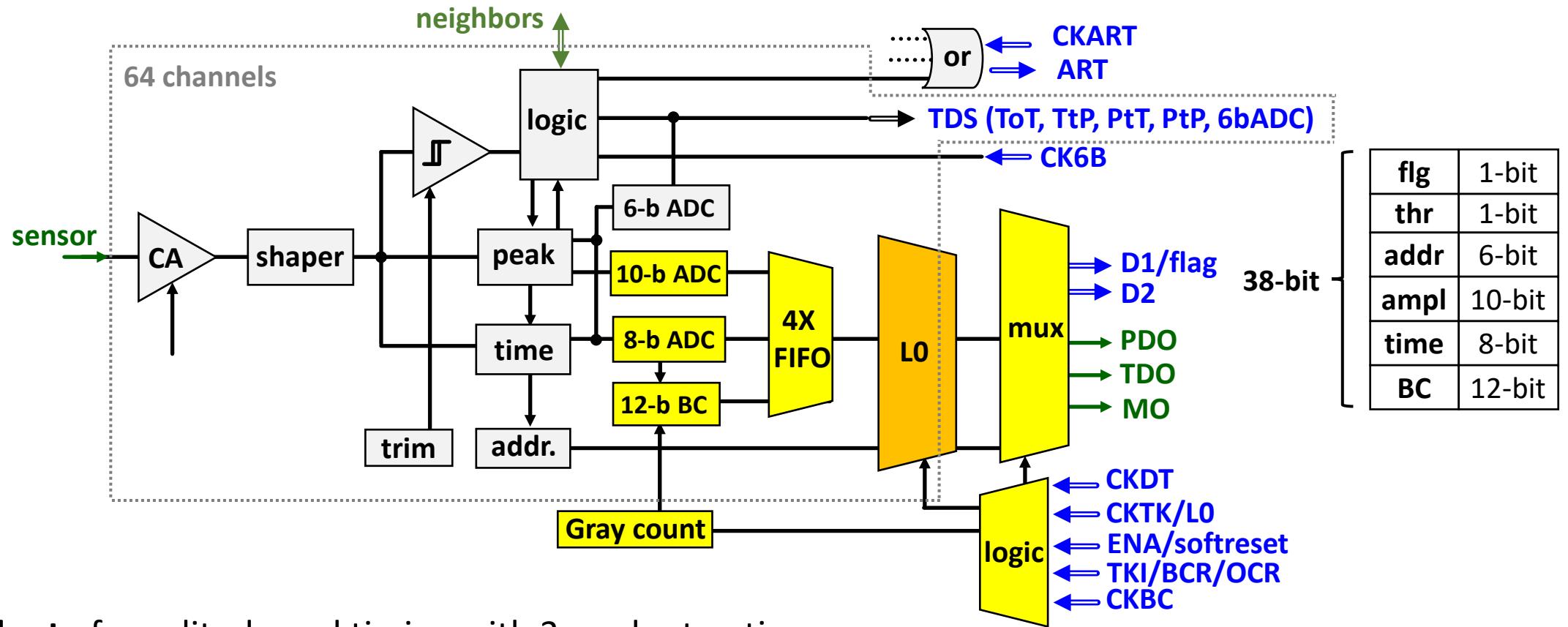


Higher Resolution 10- and 8-bit ADCs, Timestamp, Local FIFO



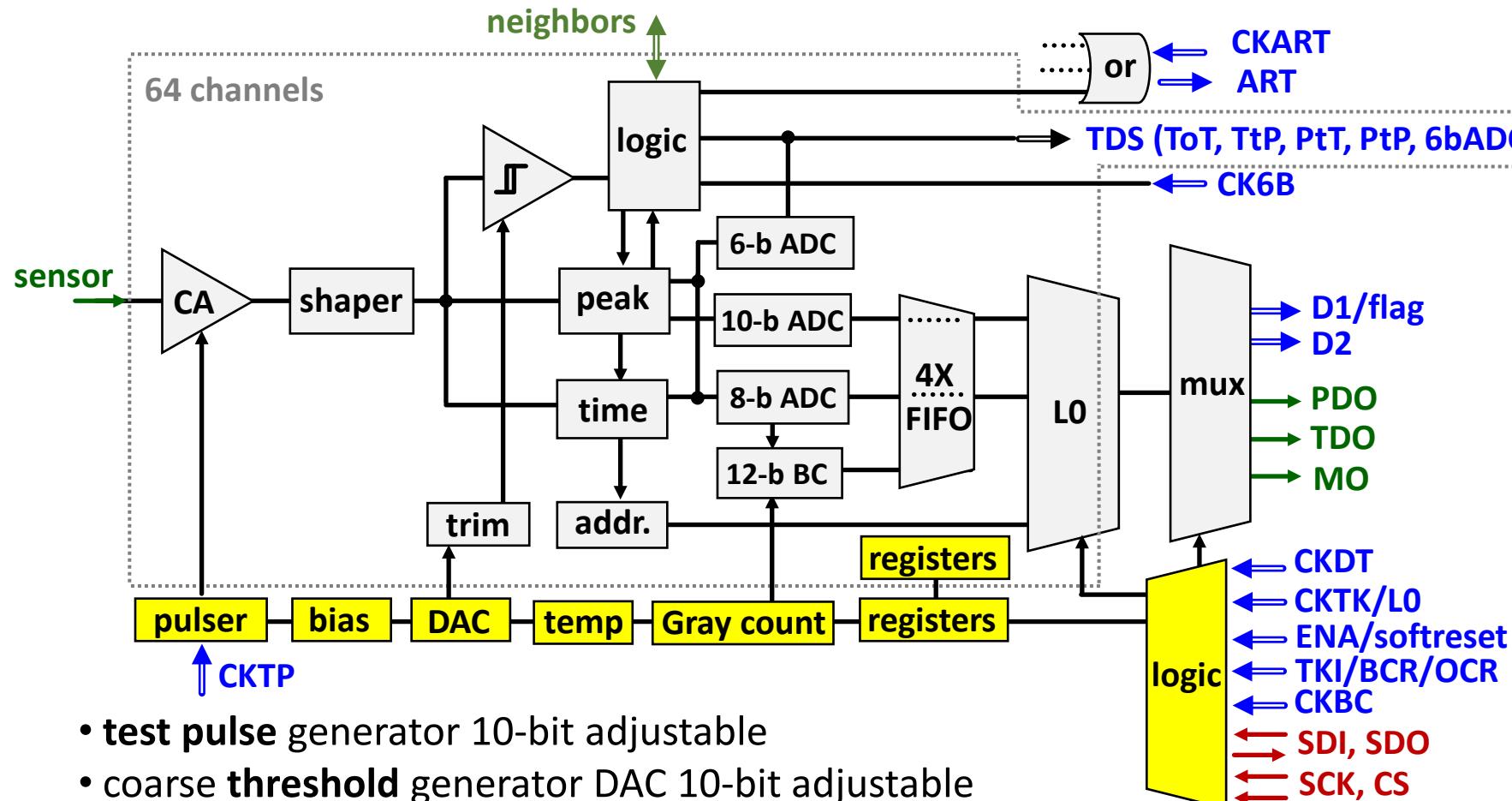
- **10-bit 200ns peak amplitude** conversion
- **8-bit 100ns fine timing** conversion of the TAC
- **12-bit coarse timestamp** from shared Gray-code counter
- full **timing information: 20-bit** ($\sim 100\mu\text{s}$ worth) with sub-ns resolution
- local **4-deep FIFO** to provide derandomization

Readout Modes and Level-0 Processor



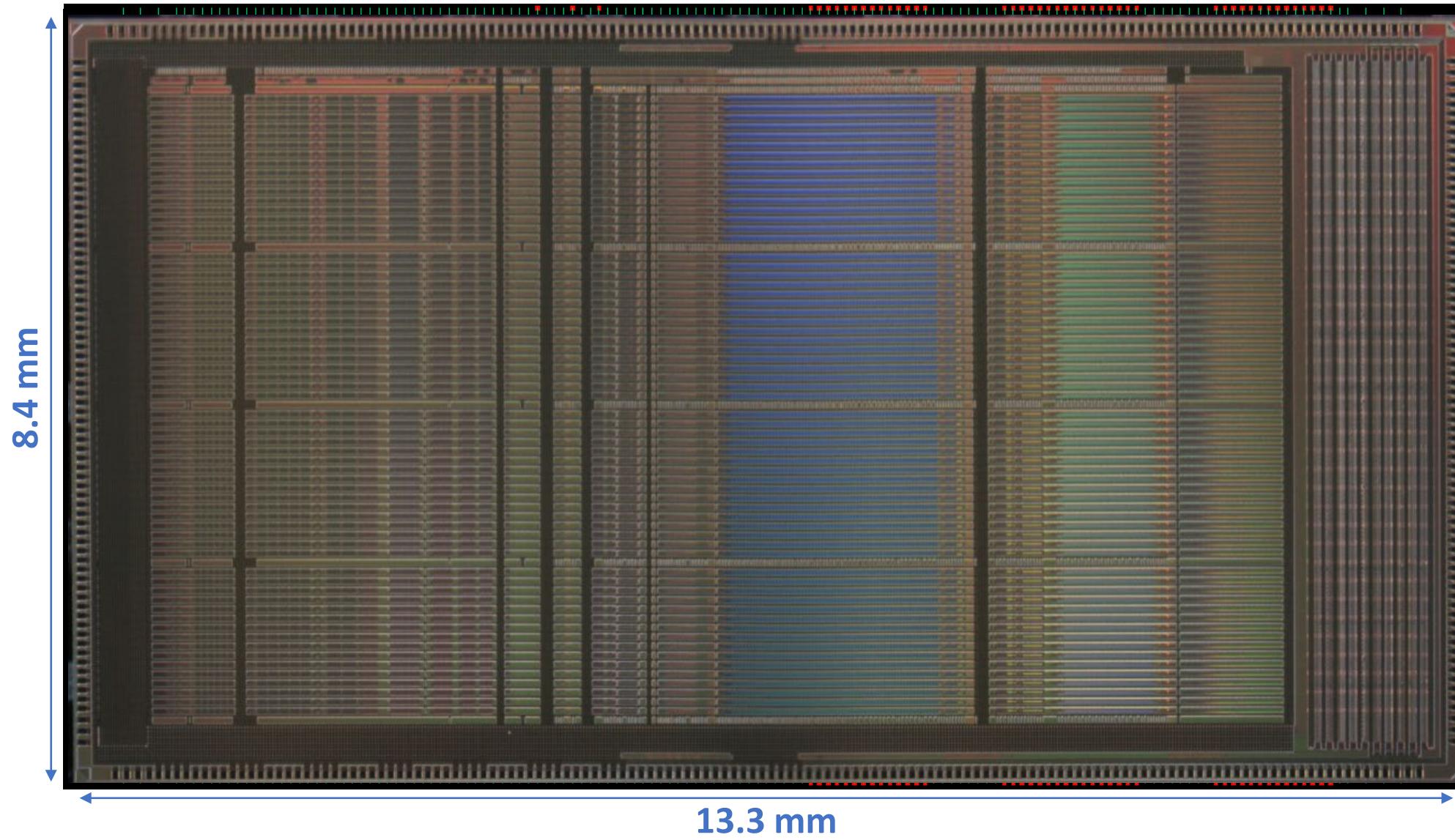
- **sparse readout** of amplitude and timing with 3 readout options:
 - a) mixed-signal **2-phase**: analog peak and timing at **PDO, TDO** and serialized address
 - b) digital **continuous**: 38-bit event data at **D1, D2, DDR** option (>1Gb/s)
 - c) **level-0 processor** (from Sorin Martoiu): NSW-specific, 64-deep latency FIFO, programmable acceptance windows, event builder, serializer, ...

Additional Functions and Shared Circuits



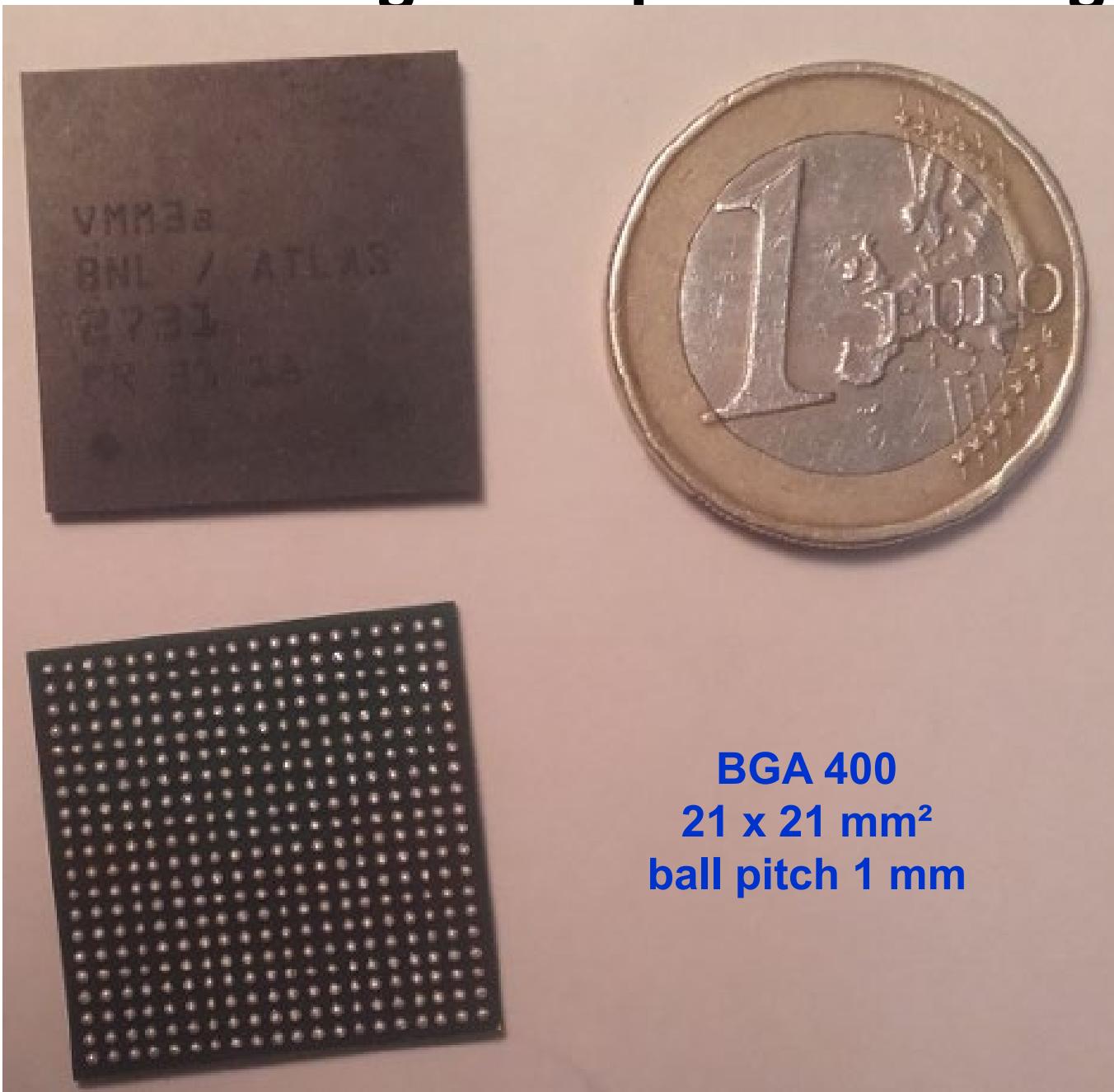
- test pulse generator 10-bit adjustable
- coarse threshold generator DAC 10-bit adjustable
- temperature sensor: $\sim 725 \text{ mV} - 1.85 \text{ mV}/^\circ\text{C}$
- analog monitor: analog signal, trimmed threshold, DACs, temperature
- configuration registers: 96-bit + 24-bit / channel
- SEU and TID tolerant circuits

Physical Layout, Pinout, Fabrication



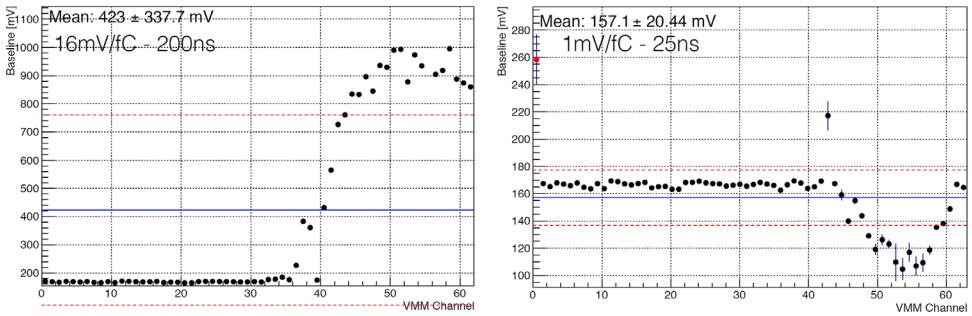
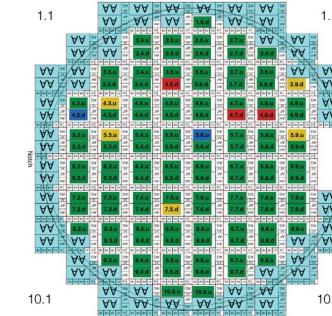
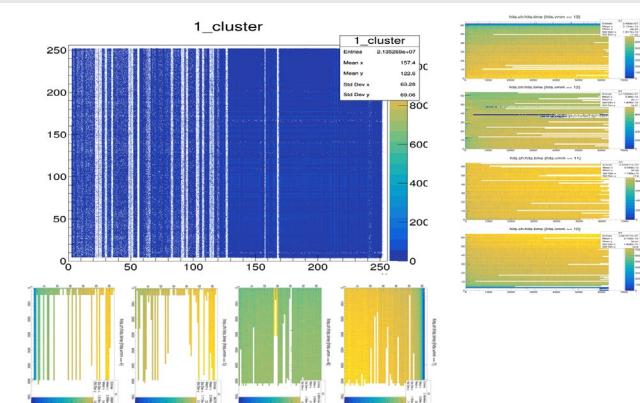
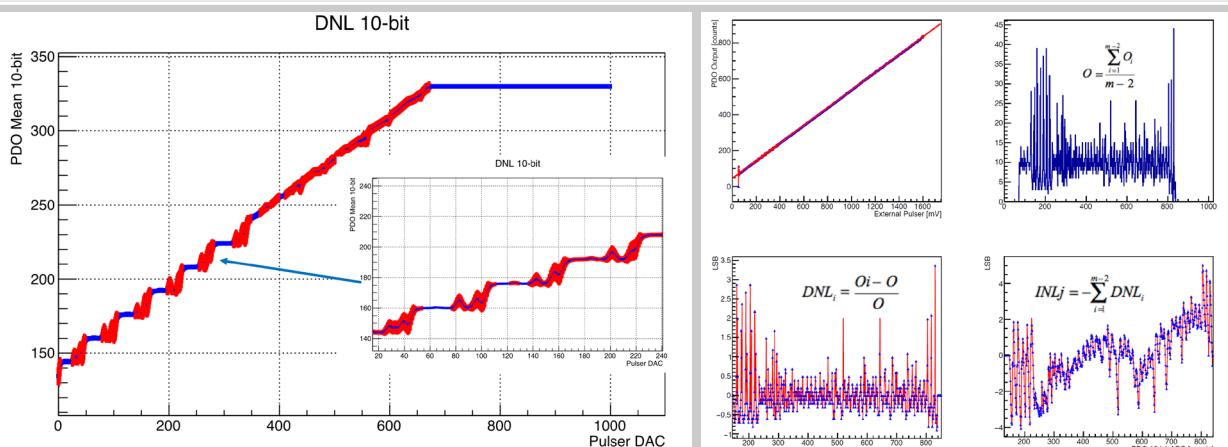
GD CMOS 130nm, power dissipation ~8-12 mW/channel (config. dependent), 10M MOSFETs

Wire Bonding and Optional Packaging



| | |
|-------------------|---------------|
| Vddp | preamp +1.2V |
| Vdd | analog +1.2V |
| Vss | analog 0V |
| V _{ddad} | ADC +1.2V |
| V _{ssad} | ADC 0V |
| Vdd | digital +1.2V |
| Vssd | digital 0V |
| | analog in |
| | analog out |
| | digital SE IO |
| + xxx - | SLVS IO |

Issues in VMM3a

| Item | Detail | Notes |
|---------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Yield | <ul style="list-style-type: none"> channel loss from abnormal gate leakage due to manufacturing problems, confirmed by GF in private communications results in ~65% yield at 100% functionality very localized issue, well understood and resolvable at design level |  <p>row.column.pos position: VV u VV d Legend: - not tested - no baseline issue - up to two channels - more than two channel - chip totally problematic - High current</p> <p>91% Perfect chips 96% Accepted 4% Failures</p>  |
| Event loss | <ul style="list-style-type: none"> first reported by Dorothea Pfeiffer @ ESS present when operating in timing-at-threshold due to logic bug results in channel loss or lock, depending on configuration very localized, well understood and resolvable with design fix |  <p>Occurring in ramp-at-threshold (SRAT=1). A time window opens from when the pulse crosses the threshold to when the peak is found. If the rising edge of CKBC doesn't occur within this time window, the stop signal doesn't get generated and the channel locks. Can be partially resolved by enabling auto-reset mode (STCR=1) plus 200ns peaktim and 650ns TAC slope. With any other peaktim or TAC setting channel loss may occur.</p> |
| ADC linearity | <ul style="list-style-type: none"> present in 8-bit and 10-bit ADCs, shows as accumulations due to missing redundancy results in effective ~7-bit resolution can be resolved by adding redundancy or by upgrading to other ADC architectures |  |

Prospects for VMM4

concurrent

| Item | Detail | Notes |
|----------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| Yield fix | localized MOSFET modification | |
| Event-loss fix | localized logic fix | re-enable local FIFO |
| ADCs upgrade | redundancy or upgraded ADCs | reduce deadtime, increase rate |
| Migration to TSMC 65nm | same 1.2V core voltage, additional metal layer | benefits: modeling, speed, noise, uniformity, power dissipation, rad. tolerance, fab. time |
| On-demand upgrades to support DRD1 detectors | <ul style="list-style-type: none"> ▪ optimized front-end and/or mixed-signal processing ▪ high-resolution modes (charge and/or timing) ▪ low-power modes ▪ higher rate capability ▪ L0-core revision or other dedicated DSP ▪ stronger ESD protections ▪ optimized digital interface ▪ additional functionality/programmability ▪ ... ▪ multiple VMM4 versions, shared fabrication | <ul style="list-style-type: none"> ▪ adjust/extend peaktimes and/or gain ranges ▪ achieve sub-100e⁻ and/or sub-10ps resolution ▪ add static/dynamic power-down options ▪ fast/parallel processing, upgraded Gb/s links ▪ multiple ad-hoc digital processing cores ▪ tailored low-parasitic configurations ▪ I2C access, multi-function IOs ▪ two VMM versions can fit one fab reticle cell |

When targeting an ASIC common to all detectors, beware of unavoidable trade-offs!

Conclusions

- VMM3a
 - versatile design with high-functionality and high-programmability
 - designed for NSW, adopted by several research groups outside ATLAS
 - affected by few understood, localized and fixable issues
 - design modularity makes it suitable for revisions and upgrades
- **VMM4**
 - fixes (yield, timing-at-threshold, ADCs)
 - design migration to TSMC 65nm
 - on-demand upgrades to support DRD1 detectors
 - multiple VMM4 versions as needed

Acknowledgment

Hans Muller, Jochen Kaminski

George Iakovidis, Venetios Polychronakos, Sorin Martoiu